Ultra-thin ZrO\textsubscript{2} (or Silicate) with high thermal stability for CMOS Gate Applications

ZJ Luo, TP Ma

*Yale University, Department of Electrical Engineering, New Haven, CT 06520*

E. Cartier, M. Copel

*IBM TJ Watson Research Center, Yorktown Heights, New York 10598*

T. Tamagawa, Bret Halpem

*Jet Process Corporation, New Haven, CT 06520*

In this study, we report on the electrical and physical properties of ultra-thin Zr Silicate/ZrO\textsubscript{2} films deposited by the Jet-Vapor-Deposition (JVD) process [3]. Both MOS Capacitors and NMOSFETs were successfully fabricated. It is shown that films with equivalent oxide thickness (EOT) of 1 nm possess high thermal stability, low leakage, high reliability, good electron mobility and other good electrical properties.